

INTRODUCE:

HVGT Half Bridge high voltage silicon rectifier assembly is made of high quality silicon GPP chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. High reliability design.
2. High voltage design.
3. Power frequency ratio.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. High voltage generator.
2. Industrial microwave power supply.
3. High voltage rectifier used in electrostatic cleaning.

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: screw holes M6.
3. Net weight: 1280 grams (approx).

SHAPE DISPLAY:

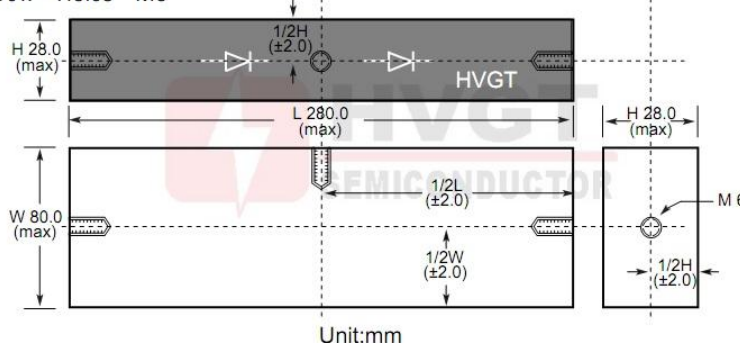


SIZE: (Unit:mm)

HVGT NAME: HVD-280

HVD-280 Series

Screw Holes M6

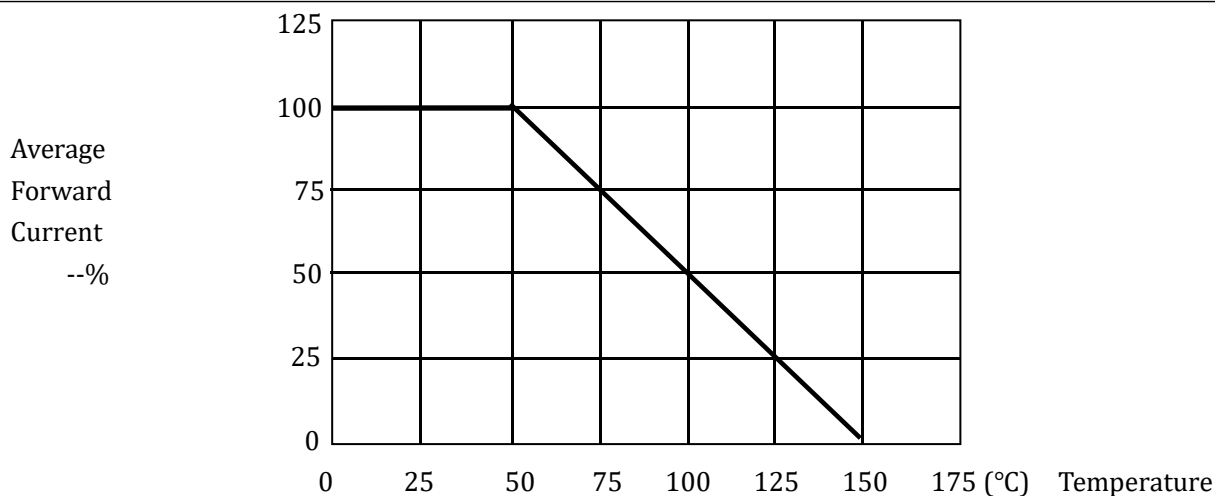
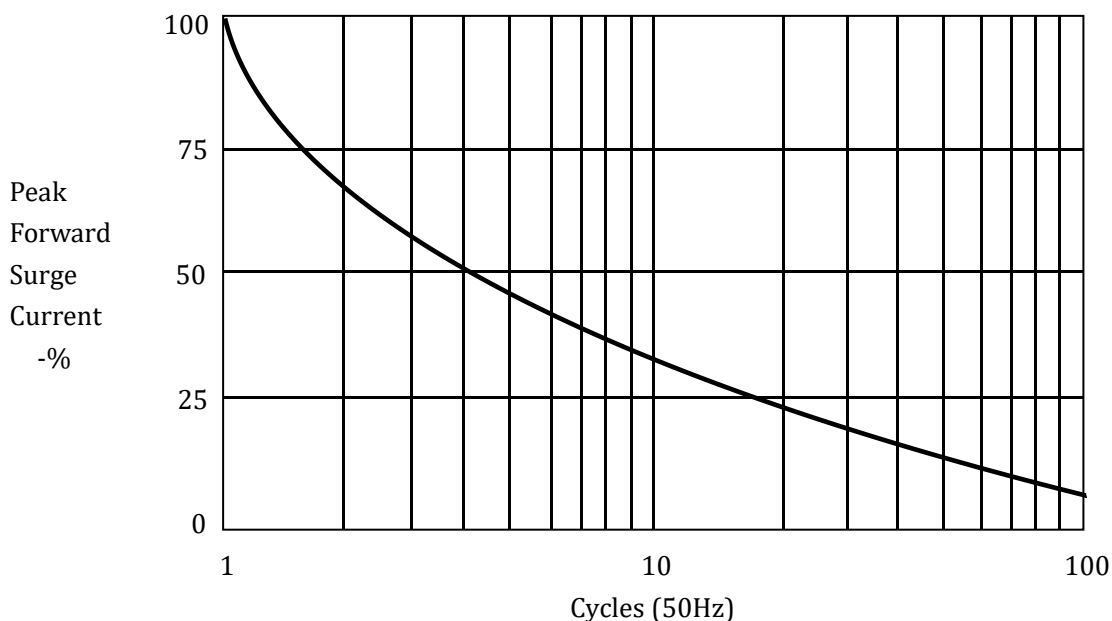


MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value		Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_A=25^{\circ}C$; $I_R=1.0\mu A$	12.0	12.0	kV
Peak Working Reverse Voltage	V_{RWM}	$T_A=25^{\circ}C$; $I_R=1.0\mu A$	12.0	12.0	kV
Non-Repetitive Peak Reverse Voltage	V_{RSM}	$T_A=25^{\circ}C$; $I_R=1.0\mu A$	14.4	14.4	kV
Average Forward Current Maximum	I_{FAVM}	$T_A=50^{\circ}C$; 50Hz Half-sine Wave; Resistance load	10		A
Non-Repetitive Forward Surge Current	I_{FSM}	$T_A=25^{\circ}C$; 50Hz Half-Sine Wave; 8.3ms	200		A
Junction Temperature	T_J		150		$^{\circ}C$
Allowable Operation Case Temperature	T_C		-40~+150		$^{\circ}C$
Storage Temperature	T_{STG}		-40~+150		$^{\circ}C$

ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

Items	Symbols	Condition	Data value		Units
Maximum Forward Voltage Drop	V_{FM}	at $25^{\circ}C$; at I_{FAVM}	13.2	13.2	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C$; at V_{RRM}	5.0		μA
	I_{R2}	at $100^{\circ}C$; at V_{RRM}	50		μA
Maximum Reverse Recovery Time	T_{RR}	at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$	--		nS
Junction Capacitance	C_J	at $25^{\circ}C$; $V_R=0V$; $f=1MHz$	--		pF

Forward Current Derating Curve

Non-Repetitive Surge Current

MARKING:

Marking	Type	Code	Cathode Mark
	HBG100D120D	HBG100D120D HVGT	

MODEL NOTE:

Type	Chip	I _{F(AV)}	Frequency	V _{RRM}	T _{RR}
HB	G	100	D	120	D
Half Bridge Series	GPP Chip	10A	D=Doubler. P=Positive Center Tap. N=Negative Center Cap.	12kV	(U)75ns (G)100ns (D) Standard Recovery Time